

High Power GaAs FET



Fujitsu Compound Semiconductor announces a new high power GaAs FET with an output of 240 W for use in the 2100 to 2200 frequency range. This device (FLL2400IU-2C) employs a push-pull design that offers ease of matching, greater consistency, and a broader bandwidth for high power amplifiers. This product is used for solid state, base-station, power amplifiers for W-CDMA and IMT 2000 Communication Systems applications. This 240W device uses enhanced GaAs power field-effect transistor process that utilizes a highly reliable gold gate (Au) metallization process with increased gain and improved third-order IM performance.

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<http://www.wirelessdesignmag.com/product-releases/2001/03/high-power-gaas-fet>